

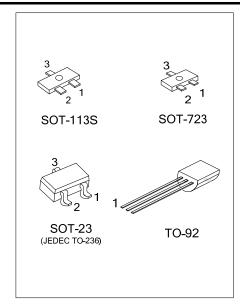
UNISONIC TECHNOLOGIES CO., LTD

2SK303 **JFET**

LOW-FREQUENCY **GENERAL-PURPOSE AMPLIFIER APPLICATIONS**

FEATURES

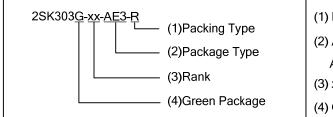
- * Ideal For Potentiometers
- * Analog Switches
- * Low Frequency Amplifiers
- * Constant Current Supplies
- * Impedance Conversion



ORDERING INFORMATION

Ordering Number		Deekees	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	2SK303G-xx-AE3-R	SOT-23	D	S	G	Tape Reel	
-	2SK303G-xx-A3C-R	SOT-113S	D	S	G	Tape Reel	
-	2SK303G-xx-AQ3-R	SOT-723	D	S	G	Tape Reel	
2SK303L-xx-T92-B	2SK303G-xx-T92-B	TO-92	G	S	D	Tape Box	
2SK303L-xx-T92-K	2SK303G-xx-T92-K	TO-92	G	S	D	Bulk	

Note: Pin Assignment: D: Drain S: Source G: Gate



- (1) B: Tape Box, K: Bulk, R: Tape Reel
- (2) AE3: SOT-23, T92: TO-92, A3C: SOT-113S

AQ3: SOT-723

- (3) x: Refer to Classification of IDSS
- (4) G: Halogen Free and Lead Free, L: Lead Free

MARKING

Package	MARKING			
TO-92	UTC K303□ G: Halogen Free Date Code			

SOT-23 / SOT-113S / SOT-723					
2SK303-V2	2SK303-V3	2SK303-V4	2SK303-V5		
V2G	V3G	V4G	V5G		

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■ ABSOLUTE MAXIMUM RATINGS (T_A =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V_{DSS}	30	V
Gate to Source Voltage		V_{GSS}	-30	V
Gate Current		l _G	10	mA
Drain Current		I _D	20	mA
Power Dissipation	SOT-23		200	
	SOT-113S/SOT-723	P _D 100 625	100	mW
	TO-92		625	
Junction Temperature		TJ	150	°C
Storage Temperature		T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Gate to Drain Breakdown Voltage	BV_GDS	I _G =-10μA	-30			V	
Drain-Source Leakage Current	I_{DSS}	V _{DS} =10V,V _{GS} =0V	0.6		12.0	mA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-20V			-1.0	nA	
ON CHARACTERISTICS							
Gate Cutoff Voltage	$V_{GS(OFF)}$	V_{DS} =10V, I_D =1 μ A		-1	-4	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{DS} =10mV, V _{GS} =0V		250		Ω	
Forward Transfer Admittance	Y _{FS}	V_{DS} =10V, V_{GS} =0V, f =1MHz	2.5	6.0		mS	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	\/ -10\/\/ -0\/f-1MI-		5		pF	
Reverse Transfer Capacitance	C _{RSS}	V_{DS} =10V, V_{GS} =0V, f =1MHz		1.5		pF	

■ CLASSIFICATION OF I_{DSS}

RANK	V2	V3	V4	V5
Inss (mA)	0.6 ~ 1.5	1.2 ~ 3.0	2.5 ~ 6.0	5.0 ~ 12.0

2SK303 JFET

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